



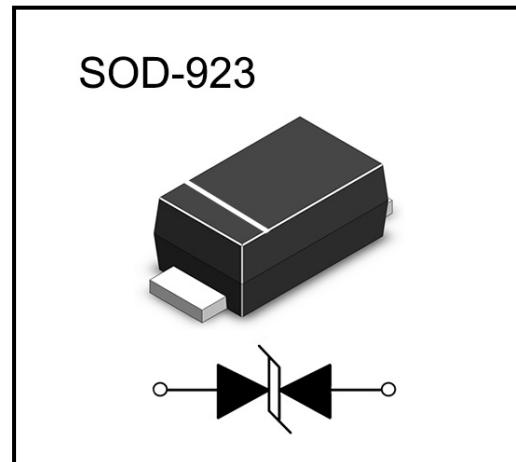
## BNLESD9D5.0CT5G

ESD Protection Diode

### Features

- 65Watts peak pulse power ( $t_p = 8/20\mu s$ )
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping Voltage
- Low leakage current
- IEC 61000-4-2  $\pm 30kV$  contact ;  $\pm 30kV$  air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20 $\mu s$ )

### Package



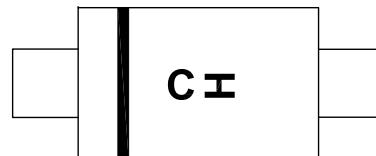
### Applications

- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Pagers Peripherals

### Mechanical Characteristics

- SOD-923 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

### Marking



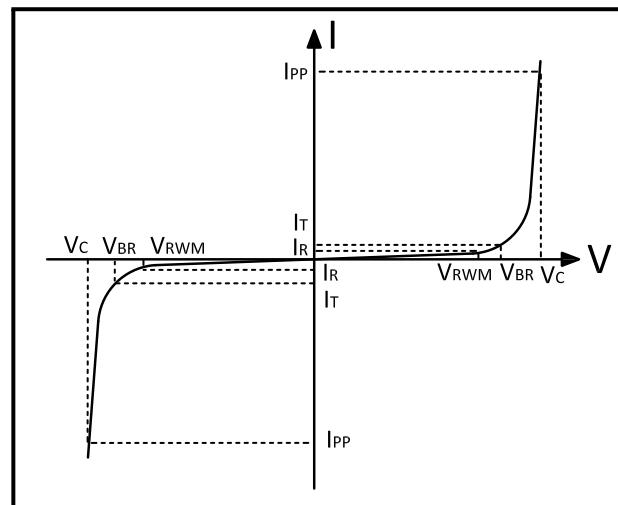
### Ordering information

Order code	Package	Base qty	Delivery mode
BNLESD9D5.0CT5G	SOD-923	10k	Tape and reel



### Electrical Parameters ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter
$I_{PP}$	Maximum Reverse Peak Pulse Current
$V_C$	Clamping Voltage @ $I_{PP}$
$V_{RWM}$	Peak Reverse Working Voltage
$I_R$	Reverse Leakage Current @ $V_{RWM}$
$V_{BR}$	Breakdown Voltage @ $I_T$
$I_T$	Test Current



Note: 8/20us pulse Waveform.

### Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power (tp = 8/20μs)	$P_{PP}$	65	Watts
Peak Pulse Current (tp = 8/20μs)	$I_{PP}$	5.0	A
ESD per IEC 61000-4-2 (Air)	$V_{ESD}$	30	KV
ESD per IEC 61000-4-2 (Contact)		30	
Lead Soldering Temperature	$T_L$	260(10seconds)	°C
Junction Temperature	$T_J$	-55 to + 150	°C
Storage Temperature	$T_{stg}$	-55 to + 150	°C

### Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	$V_{RWM}$	—	—	—	5.0	V
Reverse Breakdown Voltage	$V_{BR}$	$I_T=1\text{mA}$	6.0	7.5	9.5	V
Reverse Leakage Current	$I_R$	$V_{RWM}=5\text{V}, T=25^\circ\text{C}$	—	—	0.5	uA
Peak Pulse Current	$I_{PP}$	$tp = 8/20\mu\text{s}$	—	—	5.0	A
Clamping Voltage	$V_C$	$I_{PP}=5\text{A}, tp = 8/20\mu\text{s}$	—	11	13	V
Junction Capacitance	$C_j$	$V_R=0\text{V}, f=1\text{MHz}$	—	12	20	pF





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### Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

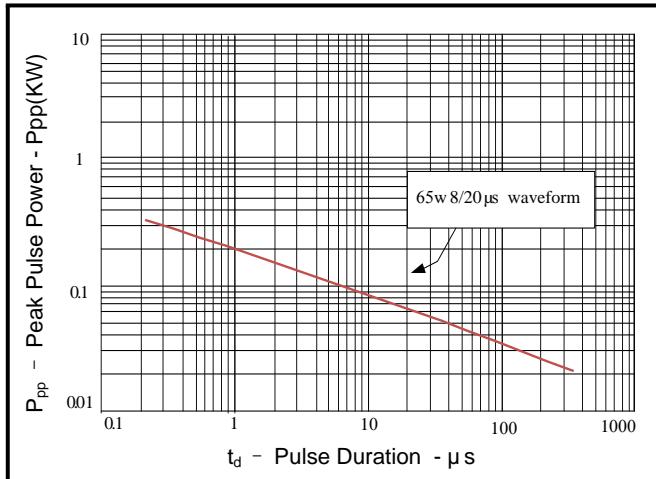


Figure 2: Power Derating Curve

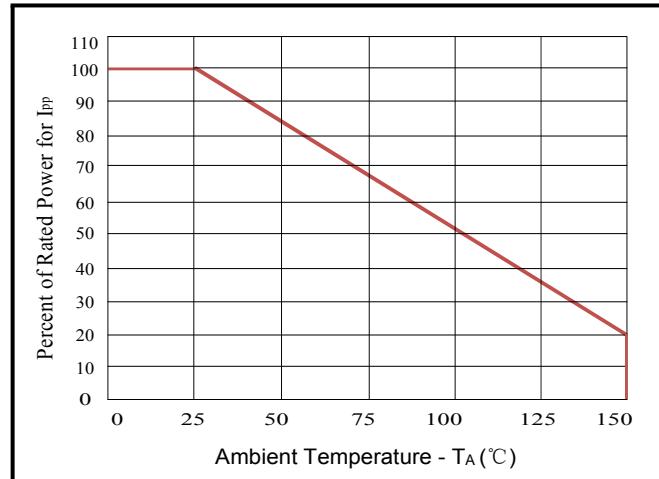


Figure 3: Pulse Waveform

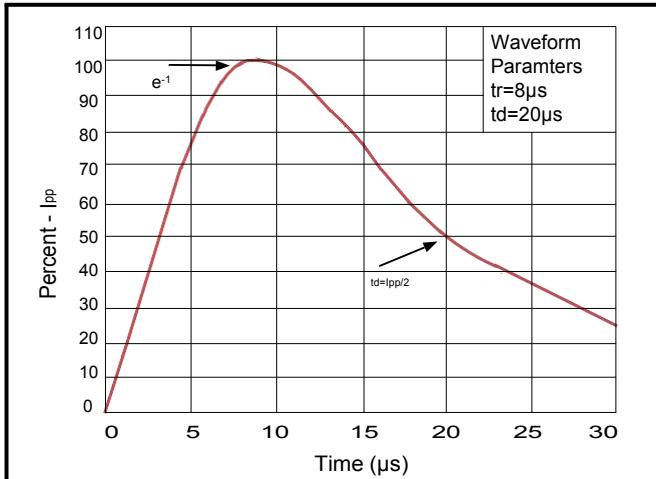
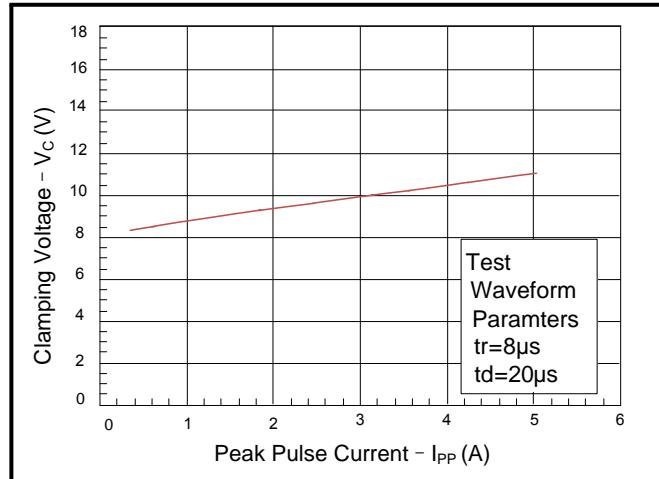


Figure 4: Clamping Voltage vs.  $I_{pp}$

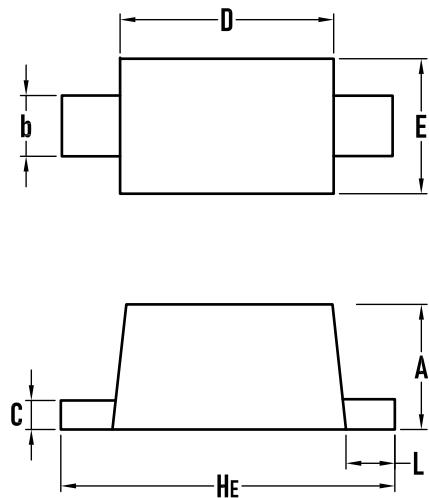




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## Outline Drawing - SOD-923



SYMBOL	MILLIMETER		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.39	0.45	0.015	0.018
b	0.15	0.30	0.006	0.012
C	0.06	0.20	0.002	0.008
D	0.70	0.90	0.028	0.035
E	0.55	0.65	0.026	0.028
HE	0.90	1.10	0.035	0.043
L	0.05	0.15	0.002	0.006

